

# High power NPN epitaxial planar bipolar transistor

### **Features**

- High breakdown voltage V<sub>CEO</sub> = 250 V
- Complementary to 2ST2121
- Typical f<sub>t</sub> = 25 MHz
- Fully characterized at 125 °C

### **Application**

■ Audio power amplifier

### **Description**

The device is a NPN transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

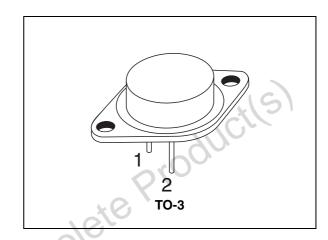


Figure 1. Internal schematic diagram

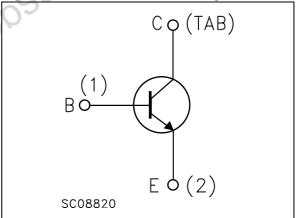


Table 1. Device summary

Order code	Marking	Package	Packaging
2ST5949	2ST5949	TO-3	tray

#### **Absolute maximum ratings** 1

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-base voltage (I <sub>E</sub> = 0)	250	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	250	V
V <sub>EBO</sub>	Emitter-base voltage ( $I_C = 0$ )	6	V
I <sub>C</sub>	Collector current	17	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	34	Α
P <sub>TOT</sub>	Total dissipation at T <sub>c</sub> = 25°C	250	W
T <sub>stg</sub>	Storage temperature	-65 to 150	Ç
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

	$T_J$	Max. operating junction temperature	150	°C	
Ta	able 3.	Thermal data		*OQ'0.	
	Symbol	Parameter		Value	Unit
	R <sub>thj-case</sub>	Thermal resistance junction-case	max	0.7	°C/W
Obsolet	e P'	Ob	Ole		

# 2 Electrical characteristics

(T<sub>case</sub> = 25 °C; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 250 V			5	μΑ
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 6 V			5	μΑ
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 50 mA	250		G.	V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage (I <sub>F</sub> = 0)	I <sub>C</sub> = 100 μA	250	401	5	V
V <sub>(BR)EBO</sub> <sup>(1)</sup>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 1 mA	6	)		V
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	$I_C = 8 \text{ A}$ $I_B = 800 \text{ mA}$			3	V
V <sub>BE</sub> <sup>(1)</sup>	Base-emitter voltage	$I_C = 7 \text{ A}$ $V_{CE} = 5 \text{ V}$			1.5	V
h <sub>FE</sub>	DC current gain	$I_{C} = 1 A$ $V_{CE} = 5 V$ $I_{C} = 7 A$ $V_{CE} = 5 V$	80 35		160	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> = 1 A V <sub>CE</sub> = 5 V		25		MHz

<sup>1.</sup> Pulsed duration = 300 μs, duty cycle ≤ 1.5%

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Electrical characteristics 2ST5949

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve

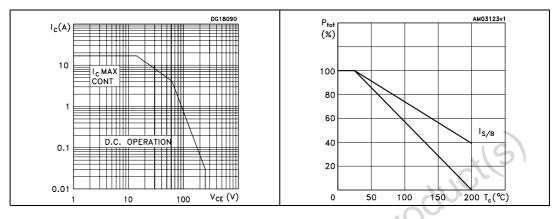


Figure 4. Output characteristics

Figure 5. DC current gain

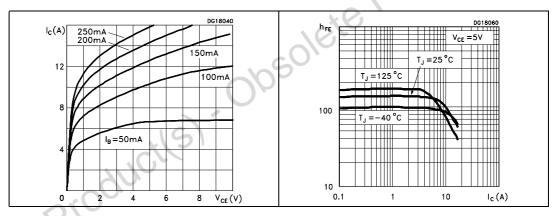
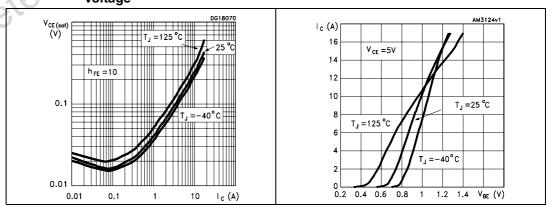


Figure 6. Collector-emitter saturation

Figure 7. Base-emitter voltage



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## 3 Package mechanical data

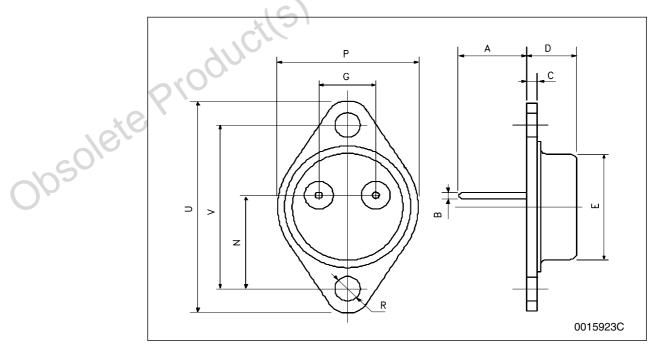
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Obsolete Product(s). Obsolete Product(s)

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TO-3	mec	hani	ical	data

DIM.	mm.				
DIWI.	min.	typ	max.		
А	11.00		13.10		
В	0.97		1.15		
С	1.50		1.65		
D	8.32		8.92		
E	19.00		20.00		
G	10.70	0'	11.10		
N	16.50		17.20		
Р	25.00	10:10	26.00		
R	4.00	60/0	4.09		
U	38.50	02	39.30		
V	30.00		30.30		



2ST5949 Revision history

# 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
05-Dec-2007	1	Initial release
05-May-2008	2	New graphics.
11-Jul-2008	3	Updated Figure 7.
17-Nov-2008	4	Content reworked to improve readability, no technical changes

Obsolete Product(s)

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